



AF/2815

PATENT
3430-0131P

IN THE U.S. PATENT AND TRADEMARK OFFICE

Applicant: Kwang-Jo HWANG Conf.:
Appl. No.: 09/648,111 Group: 2815
Filed: August 25, 2000 Examiner: BROCK II, P.
For: METHOD OF PATTERNING A METAL LAYER IN A
SEMICONDUCTOR DEVICE

LARGE ENTITY TRANSMITTAL FORMAssistant Commissioner for Patents
Washington, DC 20231

January 16, 2002

Sir:

Transmitted herewith is an amendment in the above-identified application.

- ☐ The enclosed document is being transmitted via the Certificate of Mailing provisions of 37 C.F.R. § 1.8.
- ☐ The enclosed document is being transmitted via facsimile.

The fee has been calculated as shown below:

	CLAIMS REMAINING AFTER AMENDMENT		HIGHEST NUMBER PREVIOUSLY PAID FOR		PRESENT EXTRA	RATE	ADDITIONAL FEE
TOTAL	29	-	29	=		\$18	\$0.00
INDEPENDENT	3	-	3	=		\$84	\$0.00
<input type="checkbox"/> FIRST PRESENTATION OF A MULTIPLE DEPENDENT CLAIM						\$280	\$0.00
						TOTAL	\$0.00

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- ☐ Petition for () month(s) extension of time pursuant to 37 C.F.R. §§ 1.17 and 1.136(a). \$0.00 for the extension of time.
- ☒ No fee is required.
- ☐ Check(s) in the amount of \$0.00 is(are) enclosed.
- ☐ Please charge Deposit Account No. 02-2448 in the amount of \$0.00. This form is submitted in triplicate.

If necessary, the Commissioner is hereby authorized in this, concurrent, and future replies, to charge payment or credit any overpayment to Deposit Account No. 02-2448 for any additional fees required under 37 C.F.R. § 1.16 or under 37 C.F.R. § 1.17; particularly, extension of time fees.

Respectfully submitted,

BIRCH, STEWART, KOLASCH & BIRCH, LLP

By 

Joseph A. Kolasch, #22,463

JAK/^{PLS}PLS/abs
3430-0131P

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ATTACHMENT

(Rev. 09/27/01)



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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE
MAIL ROOM

APPLICANT(S): HWANG, Kwang-Jo

SERIAL NO.: 09/648,111

GROUP: 2815

FILED: August 25, 2000

EXAMINER: Brock II, P.

FOR: METHOD OF PATTERNING A METAL LAYER IN A
SEMICONDUCTOR DEVICE

AMENDMENT

Box A.F.
Assistant Commissioner for Patents
Washington, D.C. 20231

Date: January 16, 2002

Dear Sir:

In response to the Final Office Action dated October 16, 2001, the following amendments and remarks are respectfully submitted under 37 C.F.R. §1.116 in connection with the above-identified application.

IN THE CLAIMS:

Please cancel claim 12 without prejudice or disclaimer to the subject matter contained therein.

Please amend the claims as follows:

B 13. (Amended) The method of claim 30, wherein the first plasma is a reactive gas.